



Description

The XPX6N2U9RD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

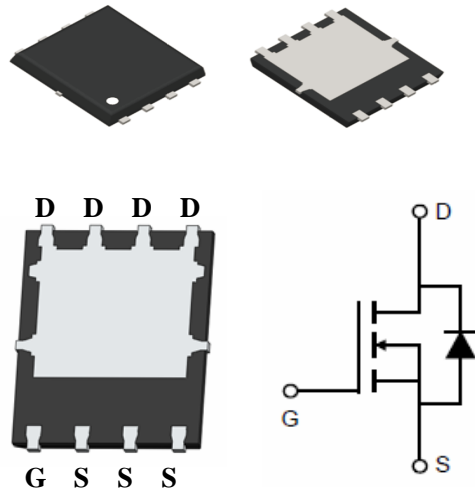
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

$V_{DS} = 60V, I_D = 120A$

$R_{DS(ON)} = 2.9m\Omega$ (typ) @ $V_{GS} = 10V$

$R_{DS(ON)} = 3.8m\Omega$ (typ) @ $V_{GS} = 4.5V$



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX6N2U9RD	XPX6N2U9RD	DFN5X6-8L	-	-	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	120	A
Drain Current-Continuous ($T_C = 100^\circ C$)	$I_D(100^\circ C)$	95	A
Pulsed Drain Current	I_{DM}	580	A
Maximum Power Dissipation	P_D	98	W
Derating factor		1.7	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	586	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.6	$^\circ C/W$

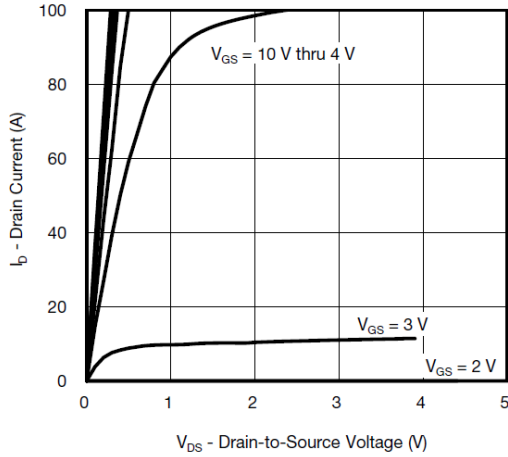
Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	2.9	3.8	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	3.8	4.8	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=20A$	50	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	3260	-	PF
Output Capacitance	C_{oss}		-	688	-	PF
Reverse Transfer Capacitance	C_{rss}		-	25	30	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=75A$ $V_{GS}=10V, R_G=4.7\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	12	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=75A,$ $V_{GS}=10V$	-	88	98	nC
Gate-Source Charge	Q_{gs}		-	13	15	nC
Gate-Drain Charge	Q_{gd}		-	14	16	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=150A$	-		1.2	V
Diode Forward Current	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = I_S$ $di/dt = 100A/\mu\text{s}$ (Note 3)	-	56		nS
Reverse Recovery Charge	Q_{rr}		-	80		nC

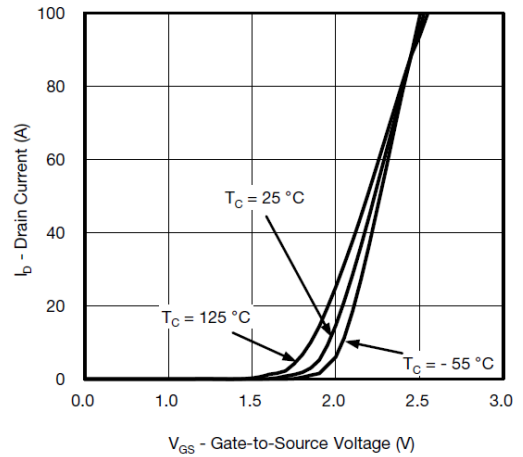
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

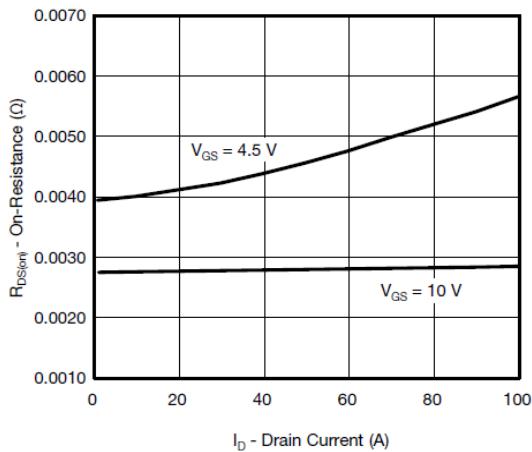
● **Typical Performance Characteristics (T_J = 25 °C, unless otherwise noted)**



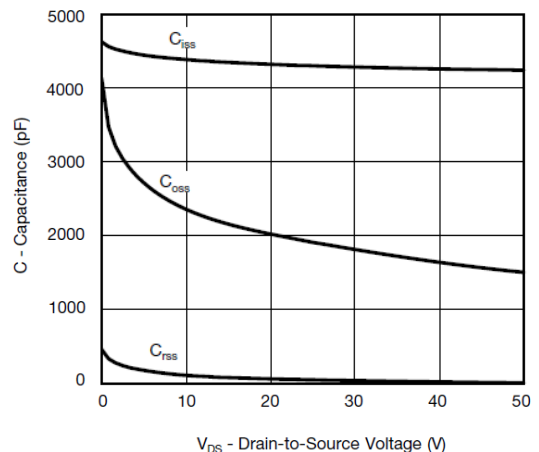
Output Characteristics



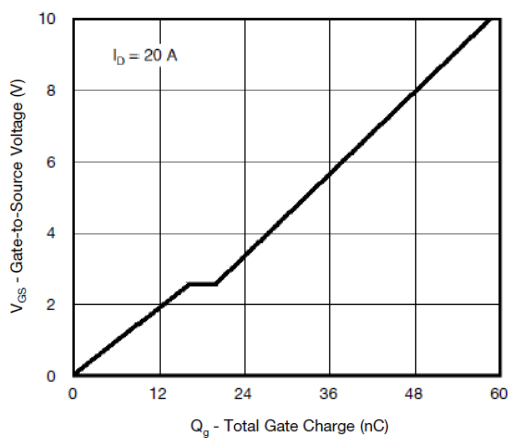
Transfer Characteristics



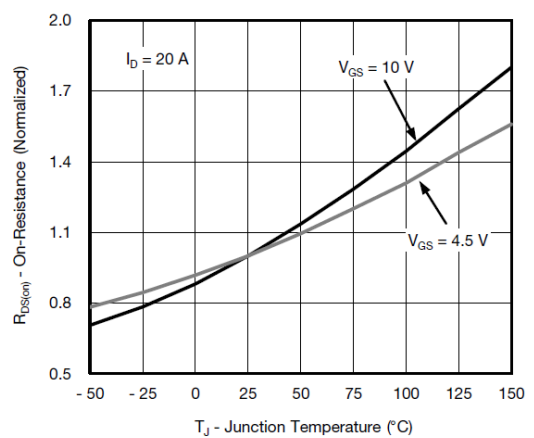
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

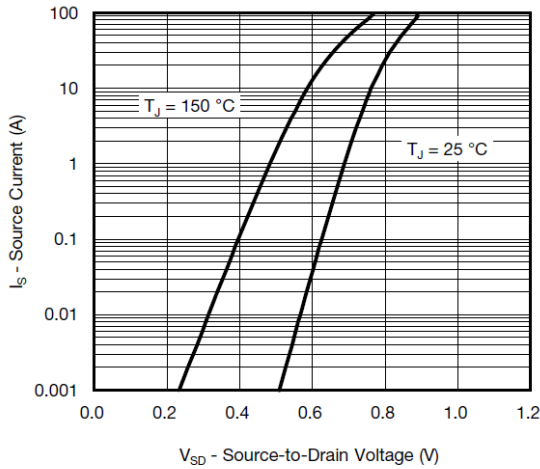


Gate Charge

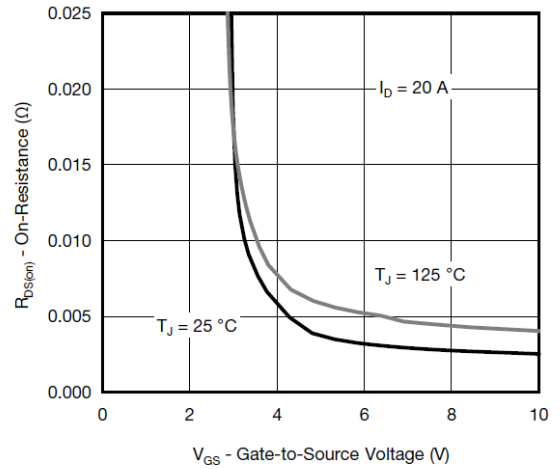


On-Resistance vs. Junction Temperature

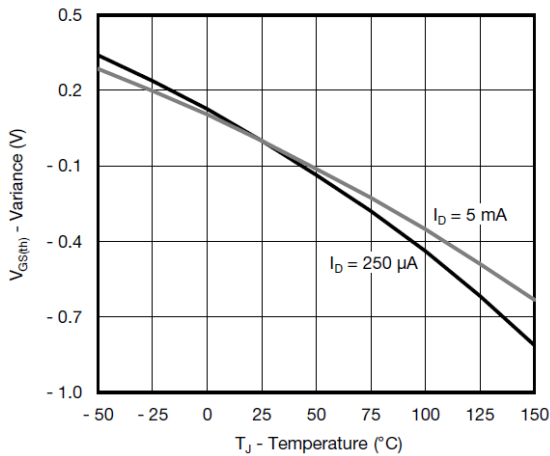
60V N-Channel Super Trench Power MOSFET



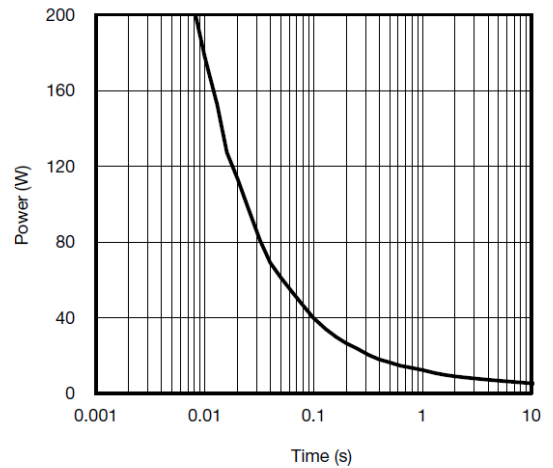
Source-Drain Diode Forward Voltage



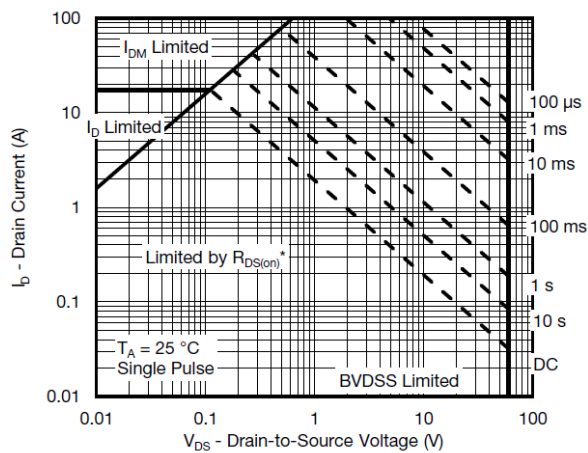
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

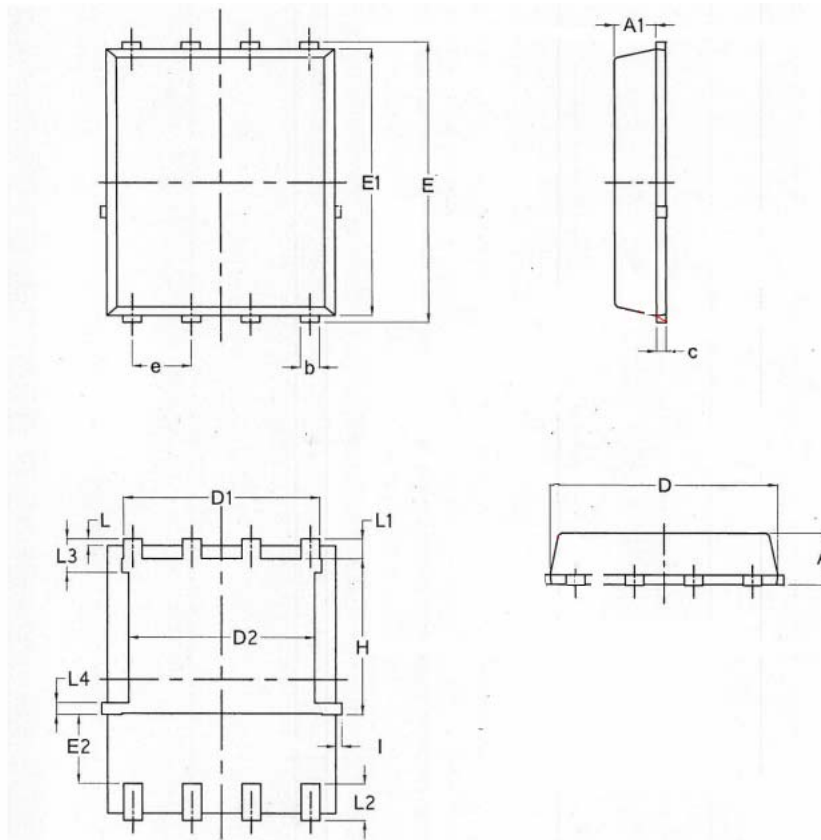


Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

DFN5X6-8L Package Information



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.90	1.10	1.17	0.0354	0.0433	0.0461
A1	0.824	0.897	0.97	0.0324	0.0353	0.0382
b	0.33	0.41	0.50	0.0130	0.0161	0.0197
C	0.150	0.20	0.250	0.0059	0.0079	0.0098
D	4.80	4.90	5.00	0.1890	0.1929	0.1969
D1	3.91	4.22	4.36	0.1539	0.1661	0.1717
D2	3.85	4.00	4.15	0.1516	0.1575	0.1634
E	5.90	60.5	6.15	0.2323	0.2382	0.2421
E1	5.65	5.76	5.85	0.2224	0.2268	0.2303
E2	1.10	/	/	0.0433	/	/
e	1.27 BSC			0.050 BSC		
L	0.05	0.15	0.25	0.0020	0.0059	0.0098
L1	0.38	0.425	0.50	0.0150	0.0167	0.0197
L2	0.51	0.785	0.86	0.0201	0.0309	0.0339
L3	0.55	0.70	0.85	0.0217	0.0276	0.0335
L4	0.10	0.25	0.40	0.0039	0.0098	0.0157
H	3.25	3.35	3.58	0.1280	0.1319	0.1409
I	0	/	0.18	0	/	0.0071

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec±1sec
Pb-Free device	260°C +0/-5°C	5sec±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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